

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	1.9611	N/A	11.0505
RT2	19.3099	N/A	1.9764
RT3	25.8667	N/A	3.9989
RT4	47.8623	N/A	9.9742
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.4486 m	N/A	7.2654 m
CT2	7.0641 m	N/A	1.7656 m
CT3	53.8282 m	N/A	1.0249
CT4	1.3823	N/A	52.2730 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	3.6561	N/A	3.1319
RF2	26.6992	N/A	11.1077
RF3	20.6825	N/A	7.1519
RF4	43.9622	N/A	5.6085
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	966.9509 u	N/A	1.5723 m
CF2	6.9415 m	N/A	4.6335 m
CF3	84.8892 m	N/A	24.5301 m
CF4	1.4438	N/A	352.6829 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

